

Nan Fang

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2899397/publications.pdf>

Version: 2024-02-01

11
papers

415
citations

1040056

9
h-index

1281871

11
g-index

11
all docs

11
docs citations

11
times ranked

693
citing authors

#	ARTICLE	IF	CITATIONS
1	Uniform and ultrathin high- κ gate dielectrics for two-dimensional electronic devices. Nature Electronics, 2019, 2, 563-571.	26.0	204
2	2D Tunnel Field Effect Transistors (FETs) with a Stable Charge-Transfer Type p^+WSe_2 Source. Advanced Electronic Materials, 2018, 4, 1800207.	5.1	41
3	Full Energy Spectra of Interface State Densities for n - and p -type MoS_2 Field-Effect Transistors. Advanced Functional Materials, 2019, 29, 1904465.	14.9	39
4	Band tail interface states and quantum capacitance in a monolayer molybdenum disulfide field-effect-transistor. Journal Physics D: Applied Physics, 2018, 51, 065110.	2.8	30
5	Accumulation-Mode Two-Dimensional Field-Effect Transistor: Operation Mechanism and Thickness Scaling Rule. ACS Applied Materials & Interfaces, 2018, 10, 32355-32364.	8.0	28
6	Hexagonal Boron Nitride As an Ideal Substrate for Carbon Nanotube Photonics. ACS Photonics, 2020, 7, 1773-1779.	6.6	22
7	Experimental detection of active defects in few layers MoS_2 through random telegraphic signals analysis observed in its FET characteristics. 2D Materials, 2017, 4, 015035.	4.4	16
8	Deterministic transfer of optical-quality carbon nanotubes for atomically defined technology. Nature Communications, 2021, 12, 3138.	12.8	16
9	Direct observation of electron capture and emission processes by the time domain charge pumping measurement of MoS_2 FET. Applied Physics Letters, 2018, 113, .	3.3	11
10	Quantum-mechanical effect in atomically thin MoS_2 FET. 2D Materials, 2020, 7, 014001.	4.4	6
11	Quantization of Mode Shifts in Nanocavities Integrated with Atomically Thin Sheets. Advanced Optical Materials, 2022, 10, .	7.3	2